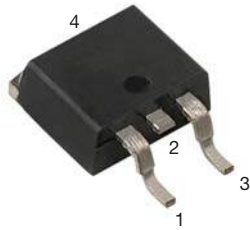
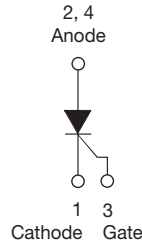




Thyristor High Voltage, Surface Mount Phase Control SCR, 16 A



TO-263AB (D²PAK)



FEATURES

- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Designed and qualified according JEDEC®-JESD 47
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS COMPLIANT HALOGEN FREE

APPLICATIONS

- Input rectification (soft start)
- Vishay input diodes, switches and output rectifiers which are available in identical package outlines

DESCRIPTION

The VS-16TTS..SPbF high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

PRODUCT SUMMARY	
Package	TO-263AB (D²PAK)
Diode variation	Single SCR
$I_{T(AV)}$	10 A
V_{DRM}/V_{RRM}	800 V, 1200 V
V_{TM}	1.4 V
I_{GT}	60 mA
T_J	-40 °C to +125 °C

OUTPUT CURRENT IN TYPICAL APPLICATIONS			
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS
NEMA FR-4 or G-10 glass fabric-based epoxy with 4 oz. (140 µm) copper	2.5	3.5	A
Aluminum IMS, $R_{thCA} = 15 \text{ °C/W}$	6.3	9.5	
Aluminum IMS with heatsink, $R_{thCA} = 5 \text{ °C/W}$	14.0	18.5	

Note

- $T_A = 55 \text{ °C}$, $T_J = 125 \text{ °C}$, footprint 300 mm²

MAJOR RATINGS AND CHARACTERISTICS			
SYMBOL	CHARACTERISTICS	VALUES	UNITS
$I_{T(AV)}$	Sinusoidal waveform	10	A
I_{RMS}		16	
V_{RRM}/V_{DRM}		800/1200	V
I_{TSM}		200	A
V_T	10 A, $T_J = 25 \text{ °C}$	1.4	V
dV/dt		500	V/µs
dI/dt		150	A/µs
T_J		-40 to +125	°C

VOLTAGE RATINGS			
PART NUMBER	V_{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V_{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I_{RRM}/I_{DRM} AT 125 °C mA
VS-16TTS08SPbF	800	800	10
VS-16TTS12SPbF	1200	1200	



ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES		UNITS	
			TYP.	MAX.		
Maximum average on-state current	$I_{T(AV)}$	$T_C = 98\text{ }^\circ\text{C}$, 180° conduction, half sine wave	10		A	
Maximum RMS on-state current	I_{RMS}		16			
Maximum peak, one-cycle, non-repetitive surge current	I_{TSM}	10 ms sine pulse, rated V_{RRM} applied	170			
		10 ms sine pulse, no voltage reapplied	200			
Maximum I^2t for fusing	I^2t	10 ms sine pulse, rated V_{RRM} applied	144		A^2s	
		10 ms sine pulse, no voltage reapplied	200			
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	$t = 0.1\text{ ms to }10\text{ ms}$, no voltage reapplied	2000		$A^2\sqrt{s}$	
Maximum on-state voltage drop	V_{TM}	10 A, $T_J = 25\text{ }^\circ\text{C}$	1.4		V	
On-state slope resistance	r_t	$T_J = 125\text{ }^\circ\text{C}$	24.0		$m\Omega$	
Threshold voltage	$V_{T(TO)}$		1.1		V	
Maximum reverse and direct leakage current	I_{RM}/I_{DM}	$V_R = \text{Rated } V_{RRM}/V_{DRM}$	$T_J = 25\text{ }^\circ\text{C}$	0.5		mA
			$T_J = 125\text{ }^\circ\text{C}$	10		
Holding current	I_H	Anode supply = 6 V, resistive load, initial $I_T = 1\text{ A}$, $T_J = 25\text{ }^\circ\text{C}$	-	150		
Maximum latching current	I_L	Anode supply = 6 V, resistive load, $T_J = 25\text{ }^\circ\text{C}$	200			
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_{J\text{ max}}$. linear to 80 % $V_{DRM} = R_g - k = \text{Open}$	500		$V/\mu s$	
Maximum rate of rise of turned-on current	dI/dt		150		$A/\mu s$	

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	P_{GM}		8.0	W	
Maximum average gate power	$P_{G(AV)}$		2.0		
Maximum peak positive gate current	$+ I_{GM}$		1.5	A	
Maximum peak negative gate voltage	$- V_{GM}$		10	V	
Maximum required DC gate current to trigger	I_{GT}	Anode supply = 6 V, resistive load, $T_J = -10\text{ }^\circ\text{C}$	90	mA	
		Anode supply = 6 V, resistive load, $T_J = 25\text{ }^\circ\text{C}$	60		
		Anode supply = 6 V, resistive load, $T_J = 125\text{ }^\circ\text{C}$	35		
Maximum required DC gate voltage to trigger	V_{GT}	Anode supply = 6 V, resistive load, $T_J = -10\text{ }^\circ\text{C}$	3.0	V	
		Anode supply = 6 V, resistive load, $T_J = 25\text{ }^\circ\text{C}$	2.0		
		Anode supply = 6 V, resistive load, $T_J = 125\text{ }^\circ\text{C}$	1.0		
Maximum DC gate voltage not to trigger	V_{GD}	$T_J = 125\text{ }^\circ\text{C}$, $V_{DRM} = \text{Rated value}$	0.25		
Maximum DC gate current not to trigger	I_{GD}		2.0		mA

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Typical turn-on time	t_{gt}	$T_J = 25\text{ }^\circ\text{C}$	0.9	μs	
Typical reverse recovery time	t_{rr}	$T_J = 125\text{ }^\circ\text{C}$	4		
Typical turn-off time	t_q		110		

THERMAL - MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range	T_J, T_{Stg}		-40 to +125	°C
Soldering temperature	T_S	For 10 s (1.6 mm from case)	260	
Maximum thermal resistance, junction to case	R_{thJC}	DC operation	1.3	°C/W
Typical thermal resistance, junction to ambient	R_{thJA}	PCB mount ⁽¹⁾	40	
Approximate weight			2	g
			0.07	oz.
Marking device		Case style D ² PAK (SMD-220)	16TTS08S	
			16TTS12S	

Note

⁽¹⁾ When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 μm) copper 40 °C/W. For recommended footprint and soldering techniques refer to application note #AN-994.

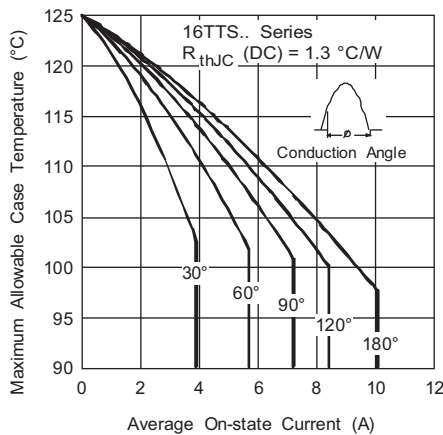


Fig. 1 - Current Rating Characteristics

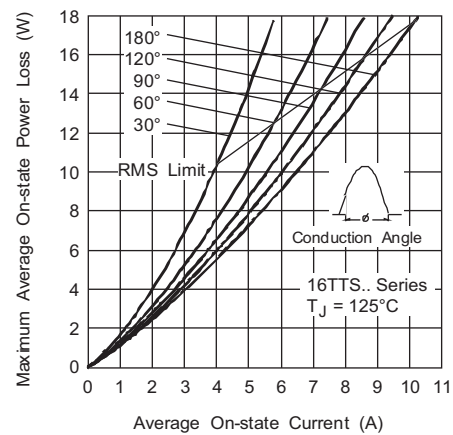


Fig. 3 - On-State Power Loss Characteristics

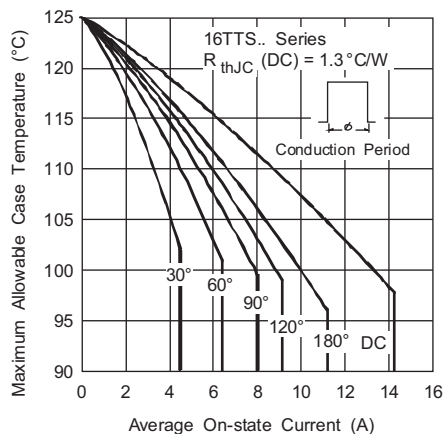


Fig. 2 - Current Rating Characteristics

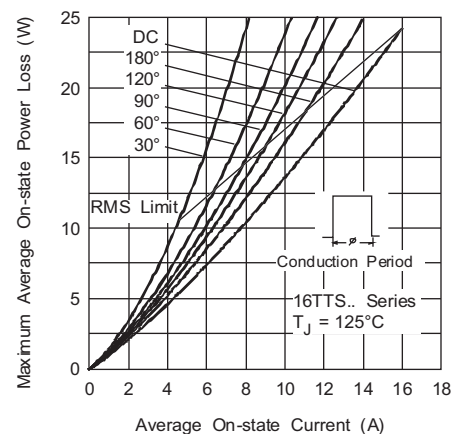


Fig. 4 - On-State Power Loss Characteristics

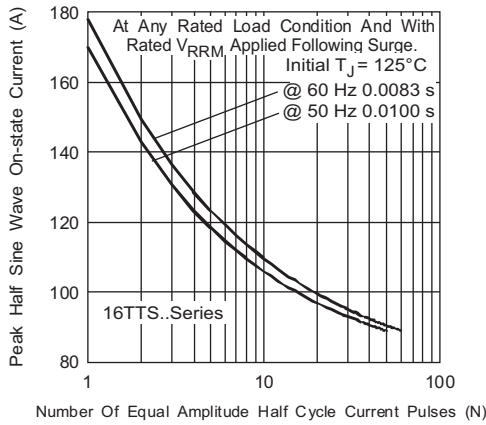


Fig. 5 - Maximum Non-Repetitive Surge Current

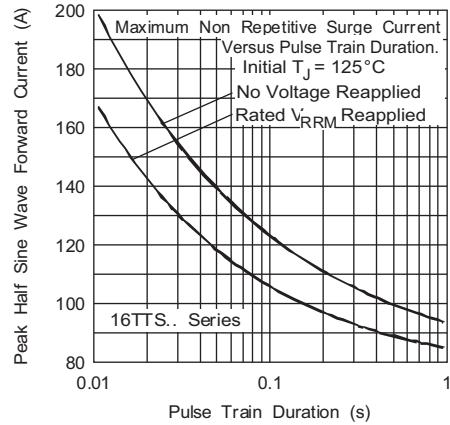


Fig. 6 - Maximum Non-Repetitive Surge Current

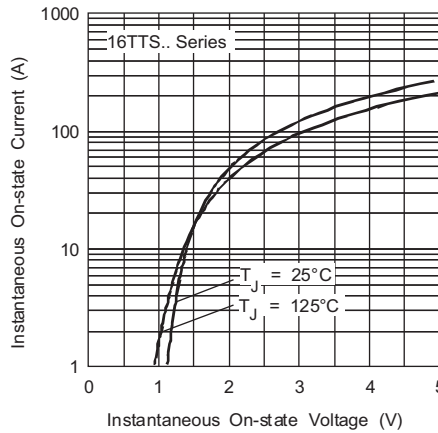


Fig. 7 - On-State Voltage Drop Characteristics

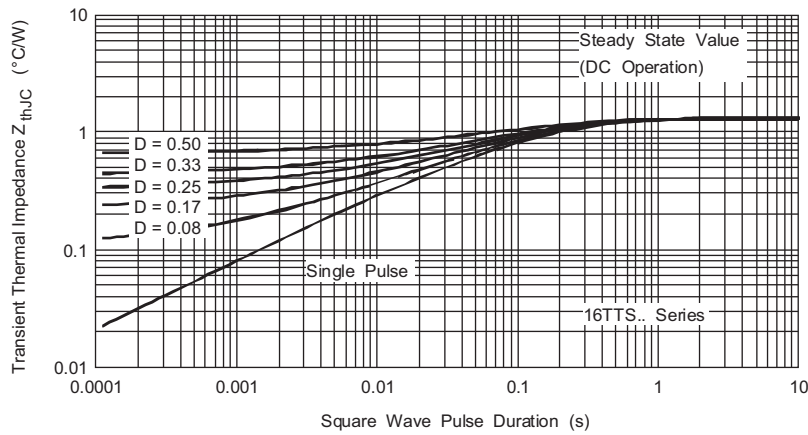


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

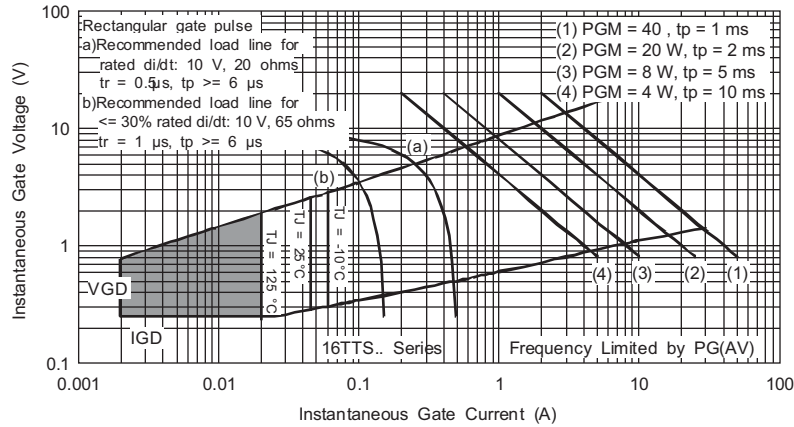


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code	VS-	16	T	T	S	12	S	TRL	PbF
	①	②	③	④	⑤	⑥	⑦	⑧	⑨

- 1** - Vishay Semiconductors product
- 2** - Current rating
- 3** - Circuit configuration:
T = single thyristor
- 4** - Package:
T = TO-220AC
- 5** - Type of silicon:
S = standard recovery rectifier
- 6** - Voltage rating: Voltage code x 100 = V_{RRM}
- 7** - S = D²PAK version
- 8** -
 - None = tube
 - TRL = tape and reel (left oriented)
 - TRR = tape and reel (right oriented)
- 9** - PbF = lead (Pb)-free and RoHS-compliant

08 = 800 V
12 = 1200 V

ORDERING INFORMATION (Example)			
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION
VS-16TTS08SPbF	50	1000	Antistatic plastic tubes
VS-16TTS08STRRPbF	800	800	13" diameter reel
VS-16TTS08STRLPbF	800	800	13" diameter reel
VS-16TTS12SPbF	50	1000	Antistatic plastic tubes
VS-16TTS12STRRPbF	800	800	13" diameter reel
VS-16TTS12STRLPbF	800	800	13" diameter reel

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95046
Part marking information	www.vishay.com/doc?95054
Packaging information	www.vishay.com/doc?95032

D²PAK

DIMENSIONS in millimeters and inches

Conforms to JEDEC® outline D²PAK (SMD-220)



SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.			MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	0.160	0.190		D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010		E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039		E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4	e	2.54 BSC		0.100 BSC		
b2	1.14	1.78	0.045	0.070		H	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4	L	1.78	2.79	0.070	0.110	
c	0.38	0.74	0.015	0.029		L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4	L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065		L3	0.25 BSC		0.010 BSC		
D	8.51	9.65	0.335	0.380	2	L4	4.78	5.28	0.188	0.208	

Notes

- Dimensioning and tolerancing per ASME Y14.5 M-1994
- Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- Thermal pad contour optional within dimension E, L1, D1 and E1
- Dimension b1 and c1 apply to base metal only
- Datum A and B to be determined at datum plane H
- Controlling dimension: inch
- Outline conforms to JEDEC® outline TO-263AB



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